BUJ302A NPN power transistor Rev. 02 — 28 March 2011



Product data sheet

Product profile 1.

1.1 General description

High-voltage, high-speed planar-passivated NPN power switching transistor in a SOT78 (TO-220AB) plastic package.

1.2 Features and benefits

- Fast switching
- High voltage capability

Low thermal resistance

1.3 Applications

- DC-to-DC converters
- High-frequency electronic lighting ballast applications
- Inverters
- Motor control systems

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _C	collector current	see Figure 1; see Figure 2; see Figure 4	-	-	4	Α
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C; see <u>Figure 3</u>	-	-	80	W
V _{CESM}	collector-emitter peak voltage	$V_{BE} = 0 V$	-	-	1050	V
Static cha	racteristics					
h _{FE}	DC current gain	I _C = 0.1 A; V _{CE} = 5 V; T _{mb} = 25 °C; see <u>Figure 11</u>	<u>[1]</u> 48	66	100	
		$I_C = 0.8 \text{ A}; V_{CE} = 3 \text{ V}; $ $T_{mb} = 25 \text{ °C}; \text{ see } \underline{\text{Figure 12}}$	<u>[1]</u> 25	42	50	

^[1] Pulse test: pulse duration \leq 300 μ s, duty cycle \leq 2 %



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	С	collector	mb	C I
3	Е	emitter		В
mb	С	mounting base; connected to collector	1 2 3	E sym123
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUJ302A	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

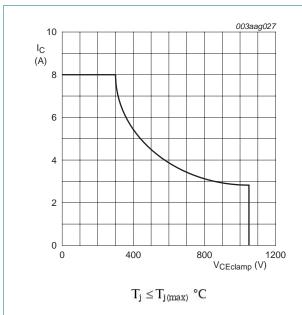
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0 V$	-	1050	V
V_{CEO}	collector-emitter voltage	I _B = 0 A	-	400	V
I _C	collector current	see Figure 1; see Figure 2; see Figure 4	-	4	Α
I _{CM}	peak collector current		-	8	Α
I _B	base current		-	2	Α
I _{BM}	peak base current		-	4	Α
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C; see <u>Figure 3</u>	-	80	W
T _{stg}	storage temperature		-65	150	°C
T _j	junction temperature		-	150	°C
V_{EBO}	emitter-base voltage	$I_C = 0 \text{ A}; I_E = 2 \text{ A}; t_p < 10 \text{ ms}$	-	24	V

BUJ302A

NPN power transistor

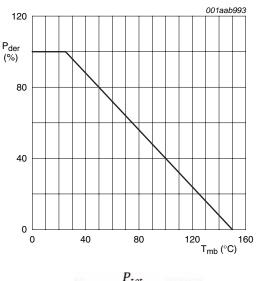


$$V_{CL(CE)} \le 1000 \ V; V_{CC} = 150 \ V; V_{BB} = -5 \ V;$$

$$L_B = 1 \ \mu H; L_C = 200 \ \mu H$$

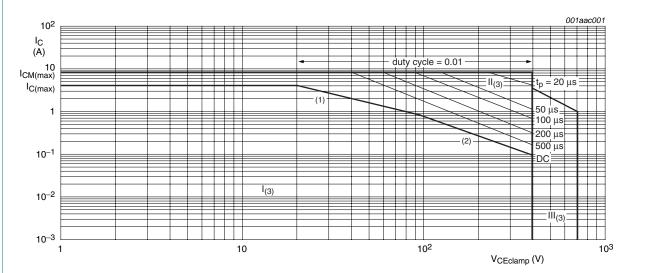
Fig 1. Reverse bias safe operating area

Fig 2. Test circuit for reverse bias safe operating area



 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$

Fig 3. Normalized total power dissipation as a function of mounting base temperature



- 1)Ptot maximum and Ptot peak maximum lines
- 2)Second breakdown limits
- 3) I = Region of permissable DC operation
 - II = Extension for repetitive pulse operation
 - III = Extension during turn-on in single transistor converters provided that RBE $\leq 100~\Omega$ and tp $\leq 0.6~\mu s$

Fig 4. Forward bias safe operating area for Tmb ≤ 25 °C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	-	1.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

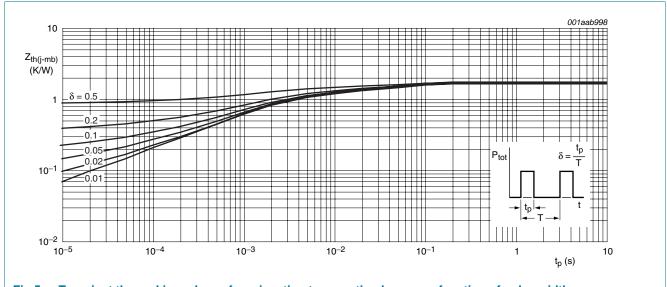


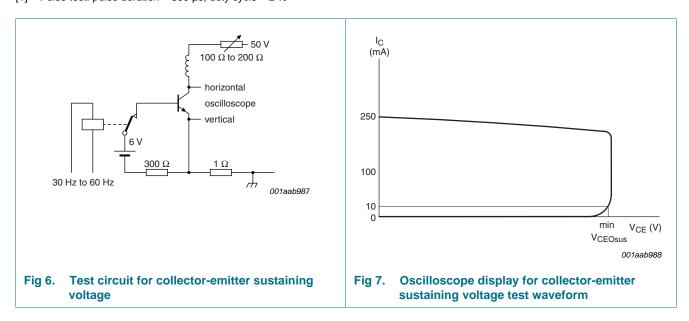
Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse width

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static cha	racteristics						
I _{CES}	collector-emitter cut-off current	$V_{BE} = 0 \text{ V}; V_{CE} = 1050 \text{ V};$ $T_{mb} = 25 \text{ °C}$		-	0.2	10	μA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 400 \text{ V}; I_{B} = 0 \text{ A}; T_{mb} = 25 \text{ °C}$		-	10	250	mA
$V_{(BR)EBO}$	open-collector emitter-base breakdown voltage	$I_B = 1 \text{ mA}; I_C = 0 \text{ A}; T_{mb} = 25 \text{ °C}$		15	19	-	V
V_{CEOsus}	collector-emitter sustaining voltage	$I_B = 0 \text{ A}$; $I_C = 10 \text{ mA}$; $L_C = 25 \text{ mH}$; $T_{mb} = 25 \text{ °C}$; see <u>Figure 6</u> ; see <u>Figure 7</u>	[1]	400	470	-	V
V _{CEsat}	collector-emitter saturation voltage	$I_C = 1 \text{ A}$; $I_B = 0.2 \text{ A}$; $T_{mb} = 25 \text{ °C}$; see Figure 8; see Figure 9	[1]	-	0.15	0.5	V
	$I_C = 3.5 \text{ A}$; $I_B = 1 \text{ A}$; $T_{mb} = 25 \text{ °C}$; see <u>Figure 8</u> ; see <u>Figure 9</u>	[1]	-	0.6	1.5	V	
V_{BEsat}	base-emitter saturation voltage	I_C = 3.5 A; I_B = 1 A; T_{mb} = 25 °C; see Figure 10	[1]	-	1.1	1.5	V
h _{FE}	DC current gain	$I_C = 0.1 \text{ A}$; $V_{CE} = 5 \text{ V}$; $T_{mb} = 25 \text{ °C}$; see Figure 11	[1]	48	66	100	
		I_C = 0.8 A; V_{CE} = 3 V; T_{mb} = 25 °C; see <u>Figure 12</u>	[1]	25	42	50	
Dynamic o	haracteristics						
ts	storage time	$I_C = 2.5 \text{ A}; I_{Bon} = 0.5 \text{ A};$		-	-	3.5	μs
t _f	fall time	I_{Boff} = -0.5 A; R_L = 60 Ω; V_{BB} = -5 V; T_{mb} = 25 °C; resistive load; t_p = 300 μs; see Figure 13; see Figure 14		-	-	500	ns

[1] Pulse test: pulse duration \leq 300 µs, duty cycle \leq 2 %



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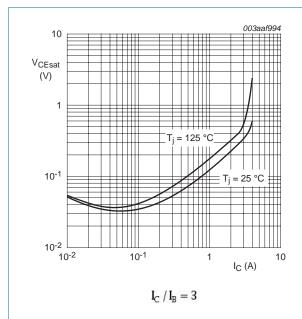


Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values

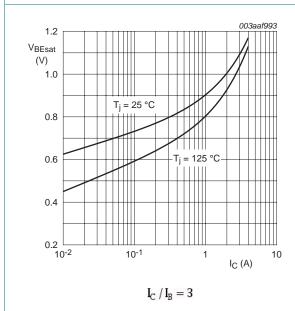


Fig 10. Base-emitter saturation voltage as a function of collector current; typical values

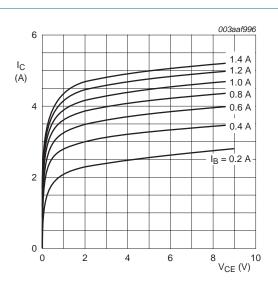


Fig 9. Collector current as a function of collector-emitter voltage; typical values

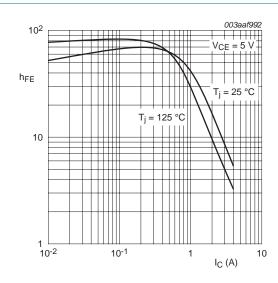


Fig 11. DC current gain as a function of collector current; typical values

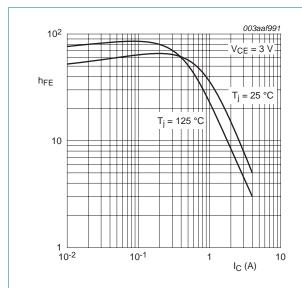
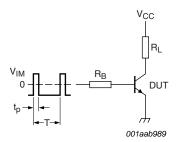


Fig 12. DC current gain as a function of collector current; typical values



 $V_{IM} = -6$ to +8 V; $V_{CC} = 250$ V; $t_p = 20$ μs ; $\delta = \frac{t_p}{T} = 0.01$ R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig 13. Test circuit for resistive load switching

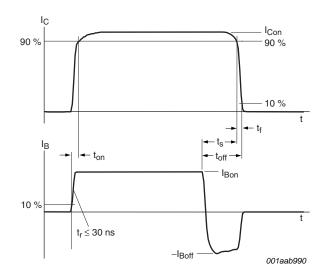
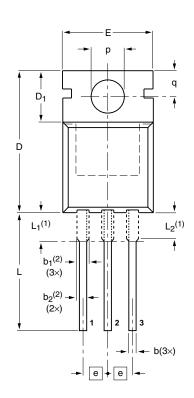
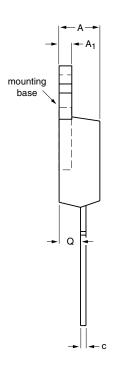


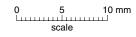
Fig 14. Switching times waveforms for resistive load

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB SOT78







DIMENSIONS (mm are the original dimensions)

UNI	T A	A ₁	b	b ₁ (2)	b ₂ (2)	С	D	D ₁	E	е	L	L ₁ (1)	L ₂ ⁽¹⁾ max.	р	q	Q	
mm	1 4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2	

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig 15. Package outline SOT78 (TO-220AB)

BUJ302A

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes					
BUJ302A v.2	20110328	Product data sheet	-	BUJ302A v.1					
Modifications:		 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 							
	 Legal texts have 	ve been adapted to the new	company name where	appropriate.					
BUJ302A v.1	19980801	Objective specification	١ -	-					

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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NPN power transistor

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